

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5359

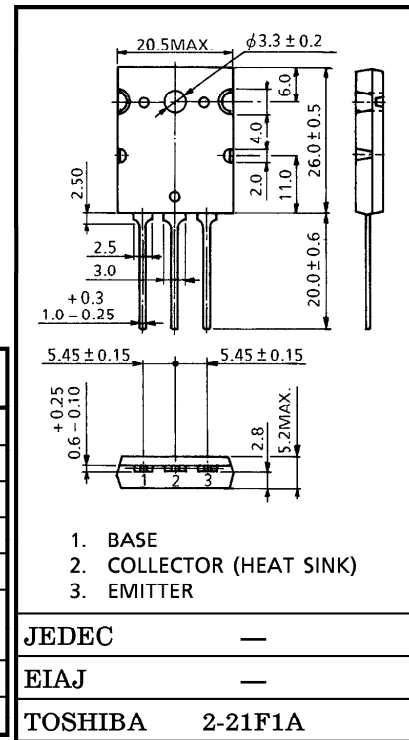
POWER AMPLIFIER APPLICATIONS

Unit in mm

- High Collector Voltage : $V_{CEO} = 230V$ (Min.)
- Complementary to 2SA1987
- Recommend for 100W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	230	V
Collector-Emitter Voltage	V_{CEO}	230	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	15	A
Base Current	I_B	1.5	A
Collector Power Dissipation (Tc = 25°C)	P_C	180	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 9.75g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 230V, I_E = 0$	—	—	5.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	5.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 50mA, I_B = 0$	230	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = 5V, I_C = 1A$	55	—	160	—
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 7A$	35	87	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 8A, I_B = 0.8A$	—	0.4	3.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 7A$	—	1.0	1.5	V
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 1A$	—	30	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	200	—	pF

(Note) $h_{FE(1)}$ Classification R : 55~110, O : 80~160

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